

Description

JMT Dual N-channel Enhancement Mode Power MOSFET

Features

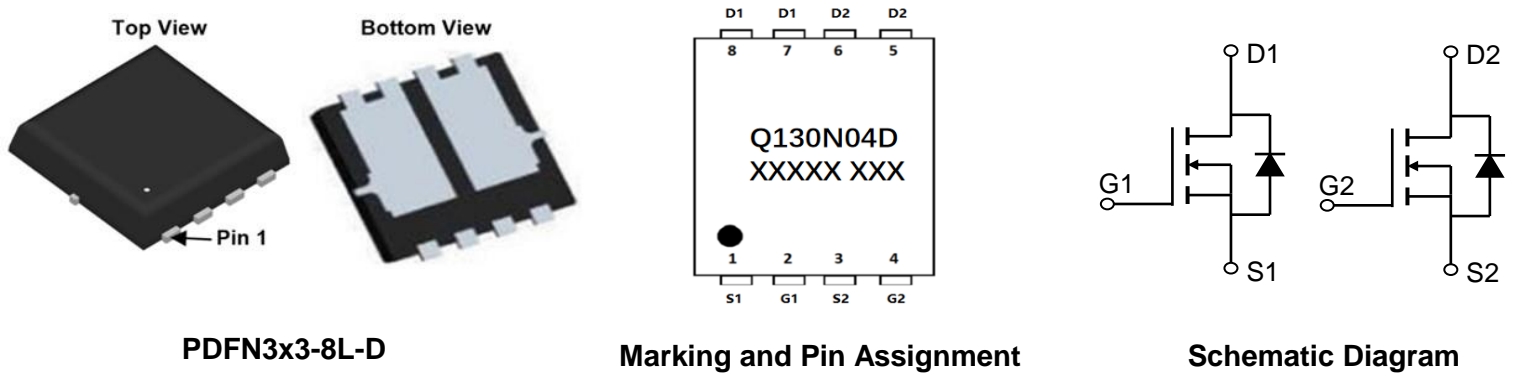
- 40V, 20A
- $R_{DS(ON)} < 19.2m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} < 25.4m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Applications

- Load Switch
- PWM Application
- Power Management



100% UIS TESTED!
100% ΔV_{ds} TESTED!



PDFN3x3-8L-D

Marking and Pin Assignment

Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
Q130N04D	JMTQ130N04D	TAPING	PDFN3x3-8L-D	13"	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	20
		$T_C = 100^\circ C$	13
I_{DM}	Pulsed Drain Current ⁽¹⁾	80	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	30	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	50
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	61	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.5	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ C$



Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 40V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.5	2.3	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	14.8	19.2	mΩ
		V _{GS} = 4.5V, I _D = 10A	-	19.5	25.4	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz	-	1342	-	pF
C _{oss}	Output Capacitance		-	87	-	pF
C _{rss}	Reverse Transfer Capacitance		-	72	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 20V, I _D = 10A	-	26	-	nC
Q _{gs}	Gate Source Charge		-	6	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 20V I _D = 10A, R _{GEN} = 3Ω	-	7	-	ns
t _r	Turn-On Rise Time		-	11	-	ns
t _{d(off)}	Turn-Off DelayTime		-	26	-	ns
t _f	Turn-Off Fall Time		-	5	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 10A, di/dt = 100A/us	-	10	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	6	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J=25C, V_{DD}=20V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=11A
 3. R_{θJA} is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

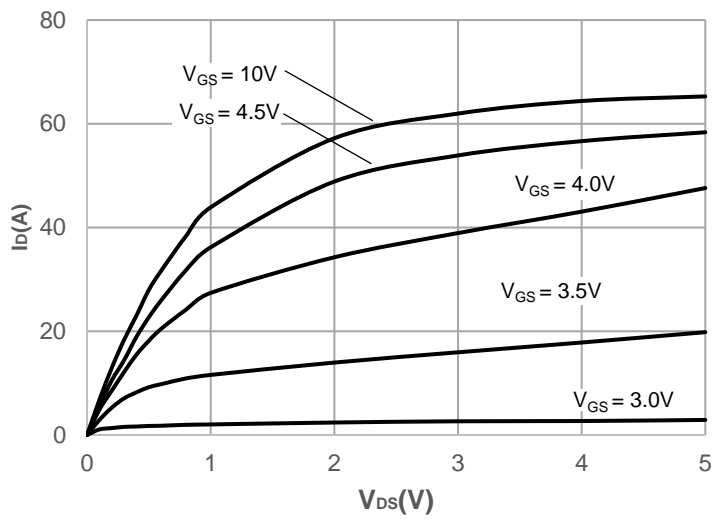


Figure 2: Typical Transfer Characteristics

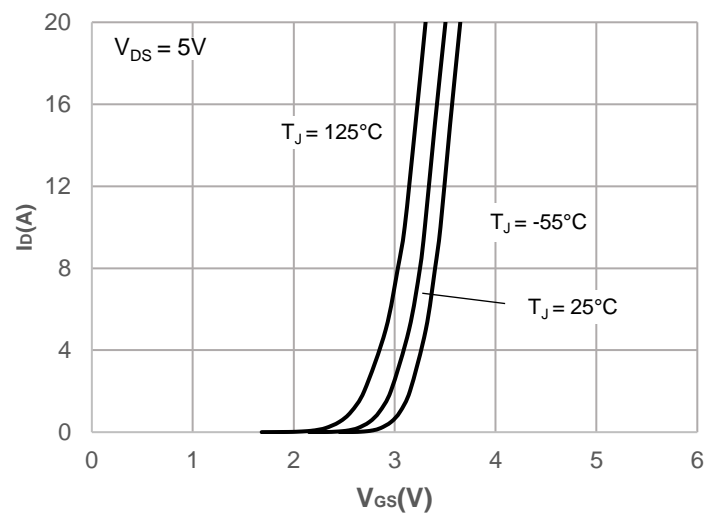


Figure 3: On-resistance vs. Drain Current

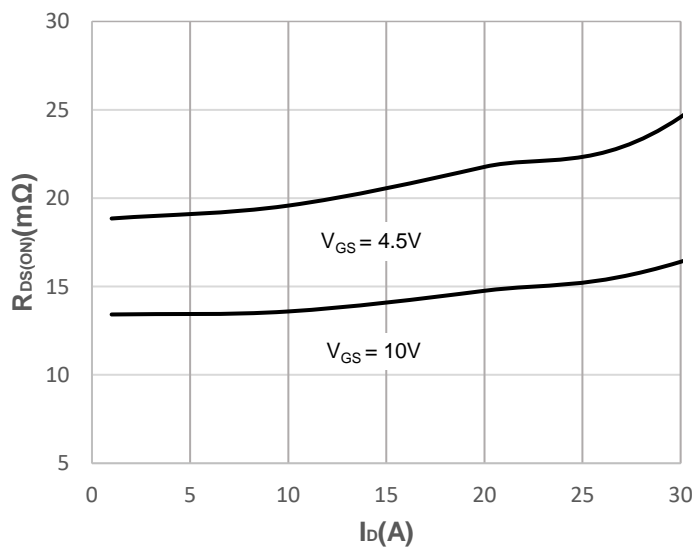


Figure 4: Body Diode Characteristics

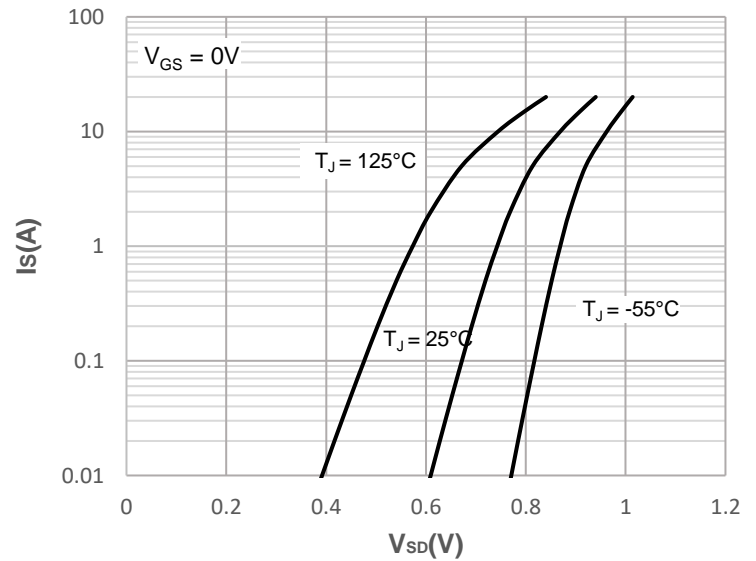


Figure 5: Gate Charge Characteristics

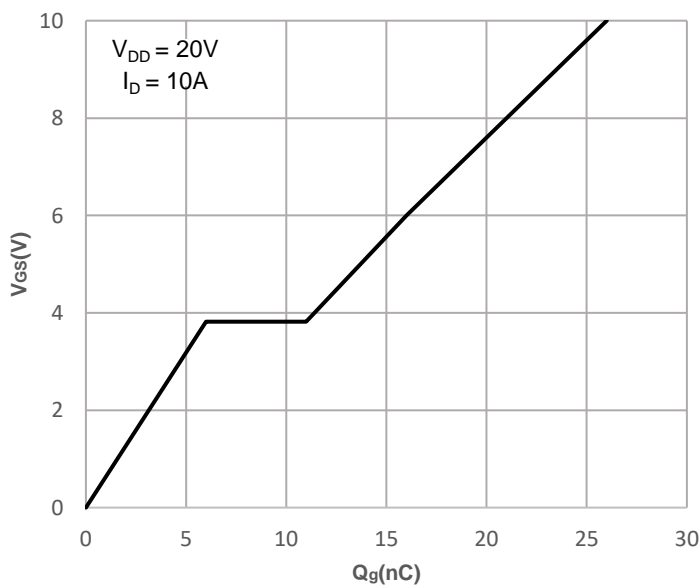
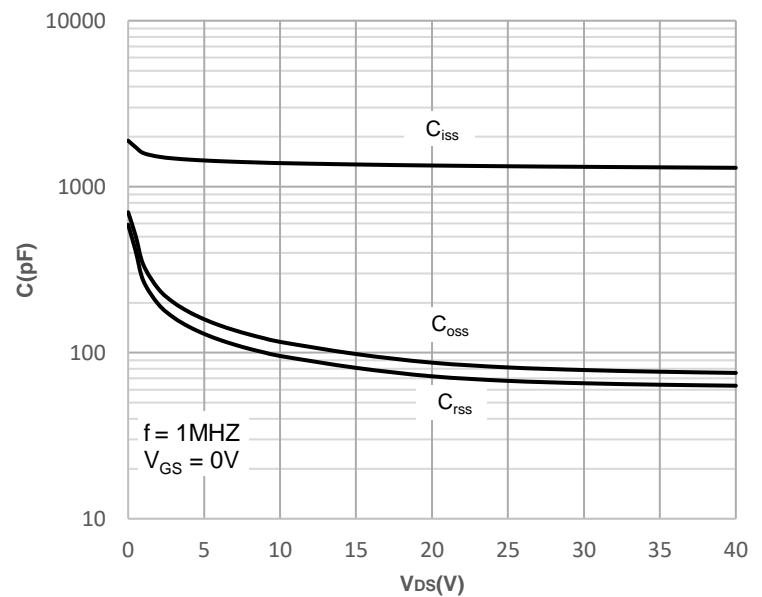


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

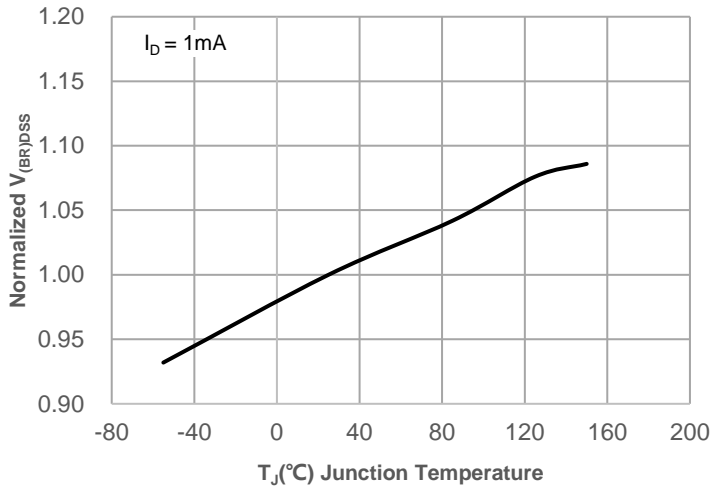


Figure 8: Normalized on Resistance vs. Junction Temperature

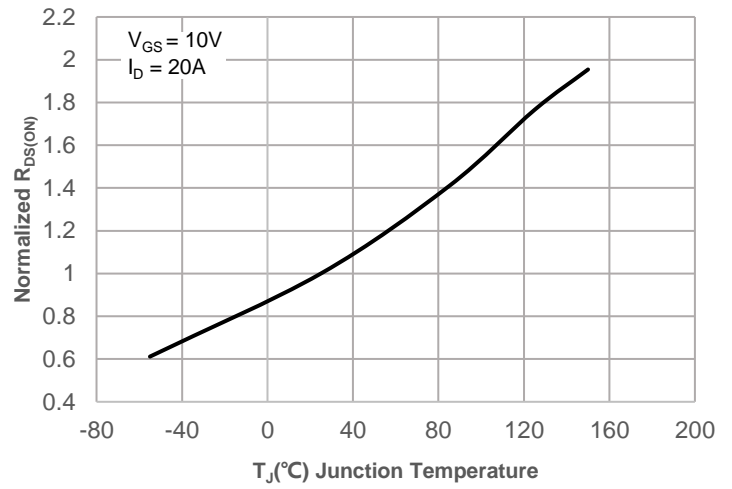


Figure 9: Maximum Safe Operating Area

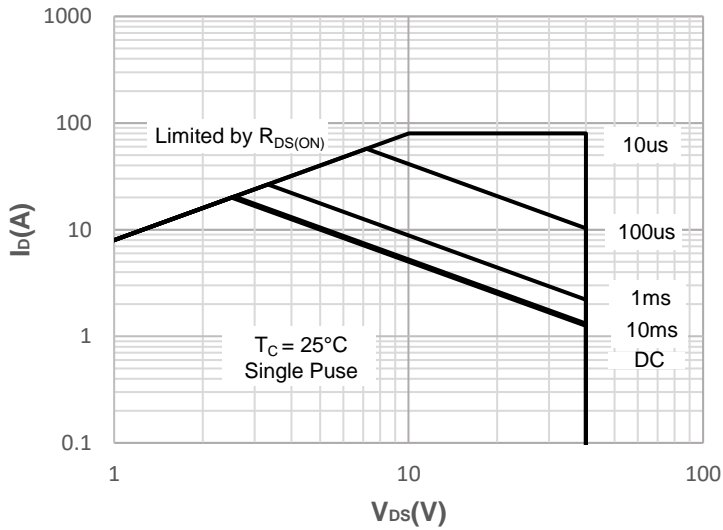


Figure 10: Maximum Continuous Driant Current vs. Case Temperature

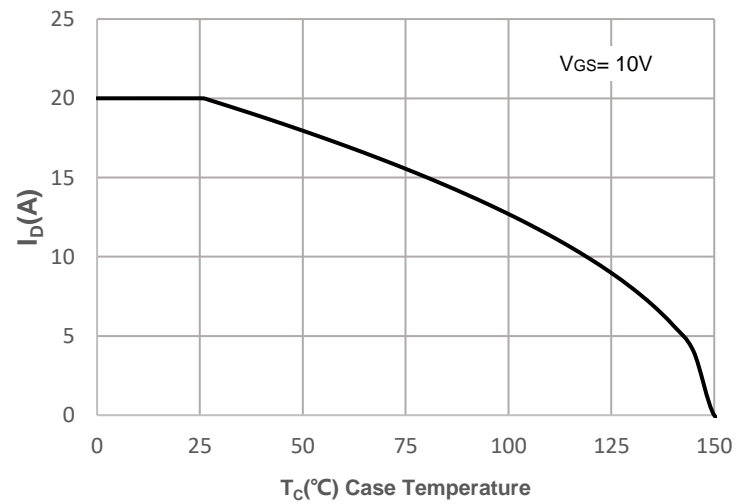


Figure 11: Normalized Maximum Transient Thermal Impedance

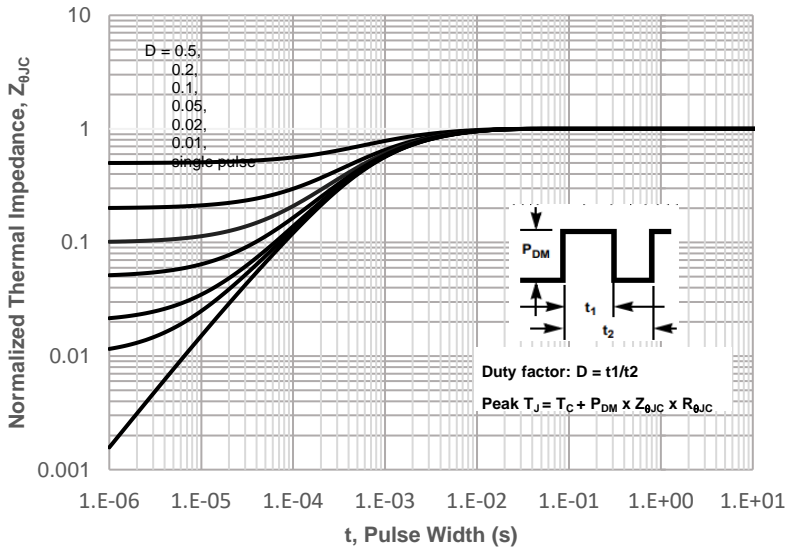
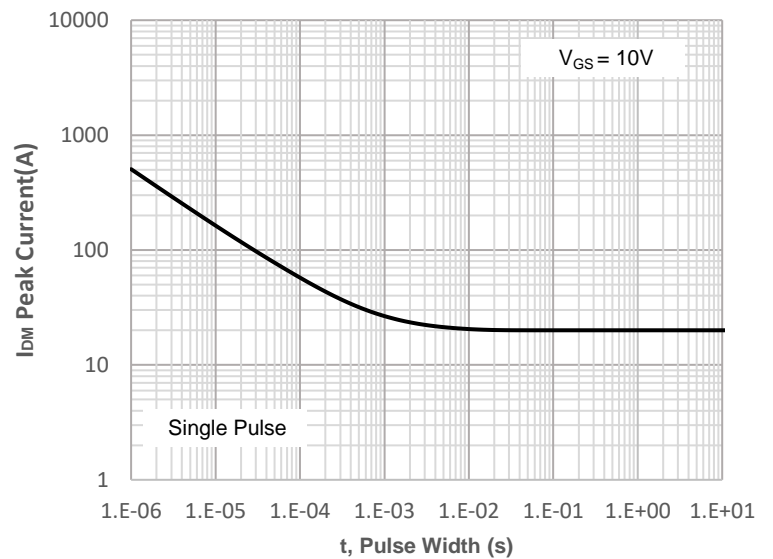


Figure 12: Peak Current Capacity



Test Circuit

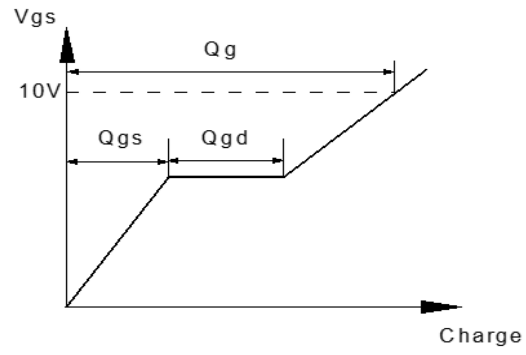
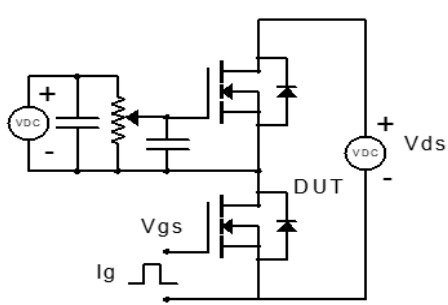


Figure 1: Gate Charge Test Circuit & Waveform

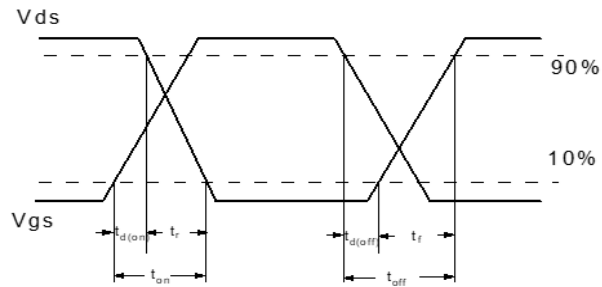
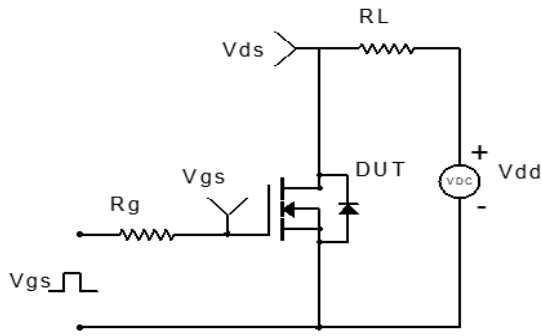


Figure 2: Resistive Switching Test Circuit & Waveform

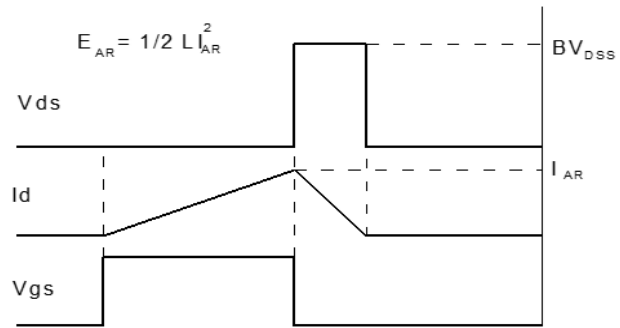
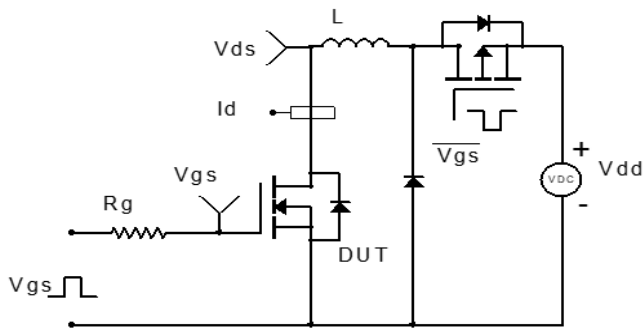


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

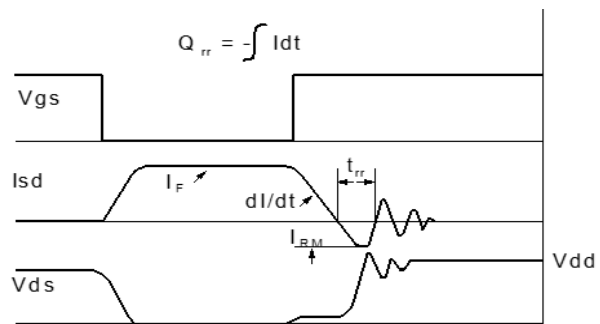
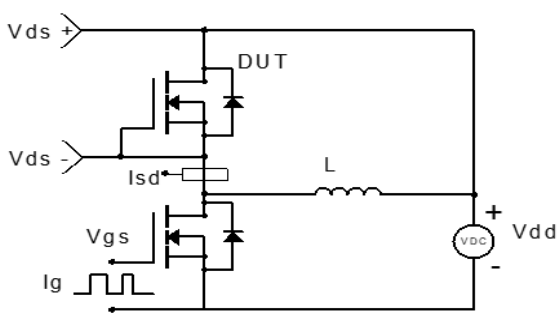
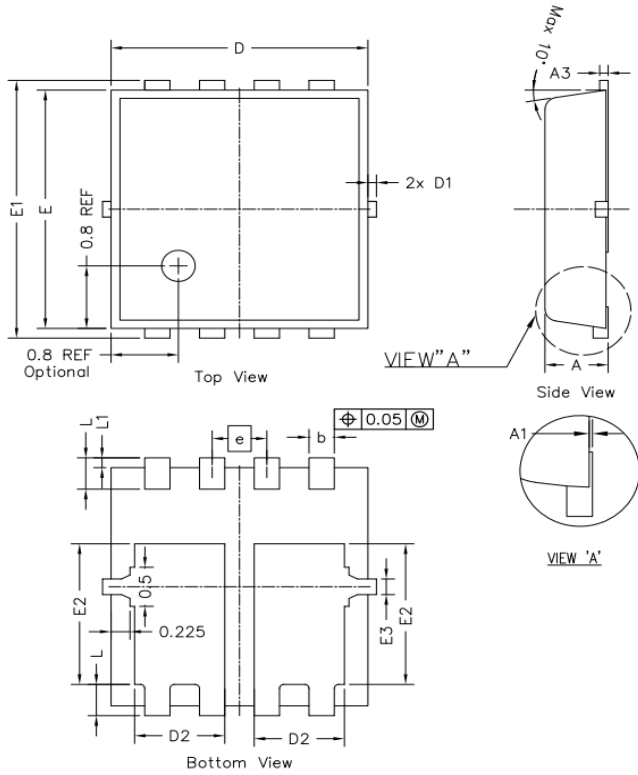


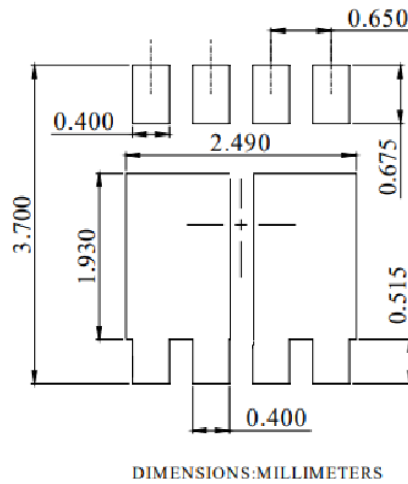
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN3x3-8L-D)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
A3	0.144	0.152	0.202	0.006	0.006	0.008
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
E	2.950	3.050	3.150	0.116	0.120	0.124
D1	---	---	0.125	----	----	0.005
E1	3.200	3.300	3.400	0.126	0.130	0.134
D2	0.970	1.070	1.170	0.038	0.042	0.046
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	0.150	0.200	0.250	0.006	0.008	0.010
L	0.300	0.400	0.500	0.012	0.016	0.020
L1	0.075	0.125	0.175	0.003	0.005	0.007

Recommended Soldering Footprint



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